

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 5)	V <sub>GS</sub> = -10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-400 -300	mA
Continuous Drain Current (Note 6)	V <sub>GS</sub> = -10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-500 -400	mA
Pulsed Drain Current (Note 5)			I <sub>DM</sub>	-1	A
Maximum Body Diode Continuous Current (Note 6)			I <sub>S</sub>	-800	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 5)	P <sub>D</sub>	0.5	W
	(Note 6)		1.2	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	255	°C/W
	(Note 6)		108	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	-1	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±10	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.3	-	-2.3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	-	2.4	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -200mA
				4		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -200mA
Diode Forward Voltage	V <sub>SD</sub>	-	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -300mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	-	51	100	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	11	20	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	9	20	pF	
Total Gate Charge	Q <sub>g</sub>	-	0.62	2	nC	V <sub>GS</sub> = -4.5V
Total Gate Charge	Q <sub>g</sub>	-	1.25	4	nC	V <sub>GS</sub> = -10V V <sub>DS</sub> = -10V, I <sub>D</sub> = -200mA
Gate-Source Charge	Q <sub>gs</sub>	-	0.16	0.5	nC	
Gate-Drain Charge	Q <sub>gd</sub>	-	0.21	0.5	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	-	4.3	10	ns	V <sub>DS</sub> = -15V, I <sub>D</sub> = -500mA V <sub>GS</sub> = -10V, R <sub>G</sub> = 1Ω
Turn-On Rise Time	t <sub>r</sub>	-	7.7	15	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	31.9	60	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	17.8	40	ns	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

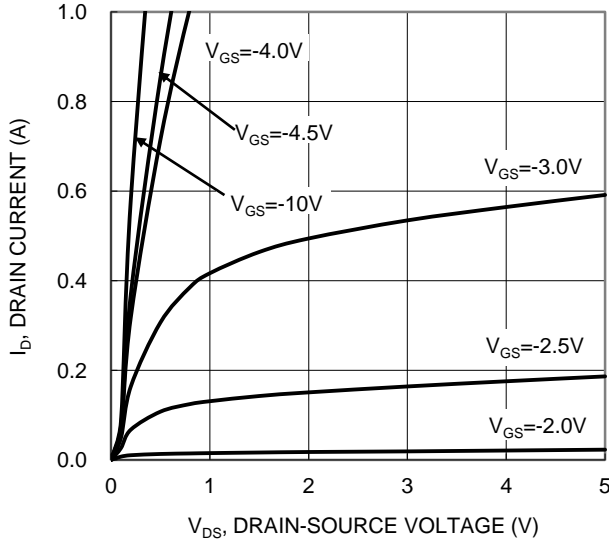


Figure 1. Typical Output Characteristic

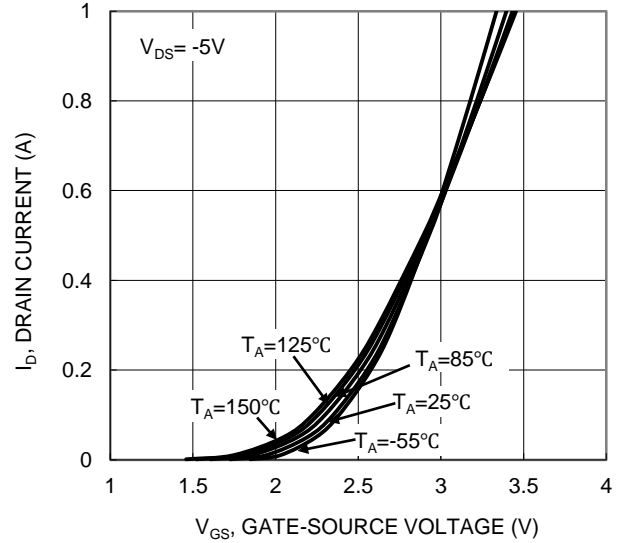


Figure 2. Typical Transfer Characteristic

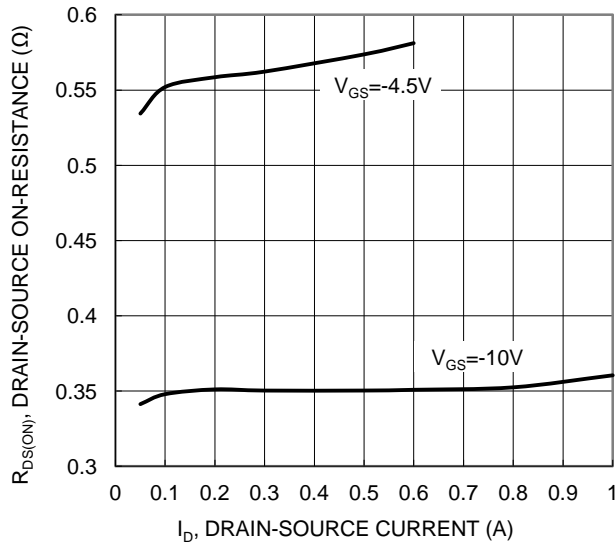


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

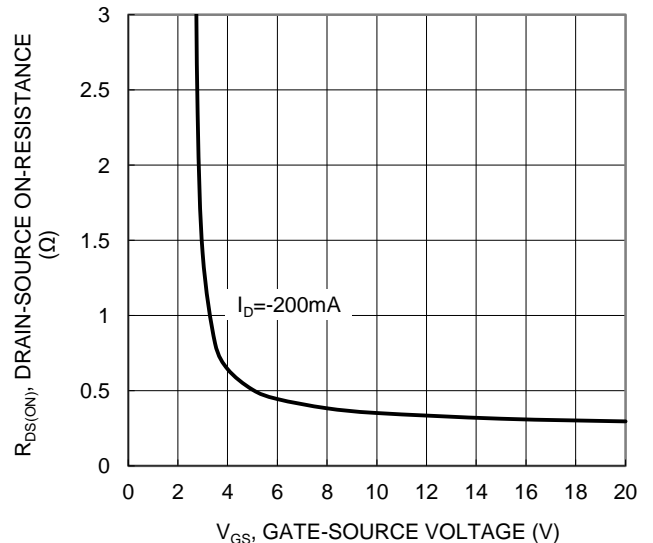


Figure 4. Typical Transfer Characteristic

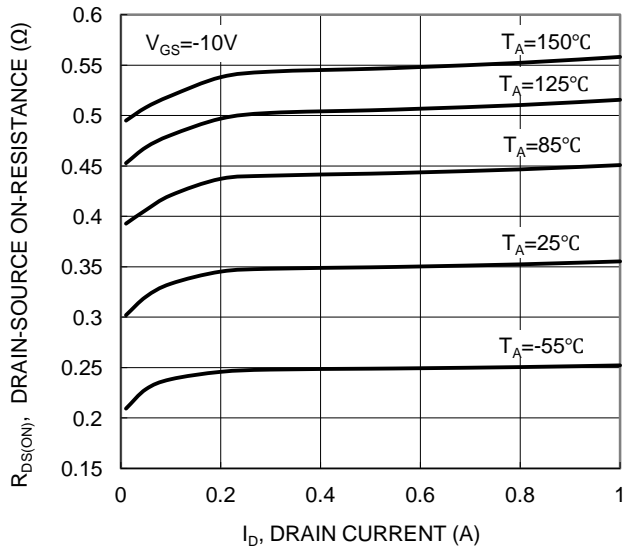


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

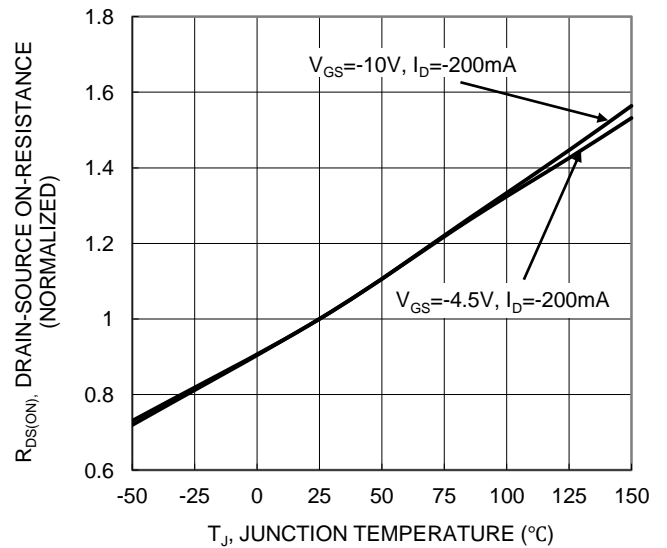
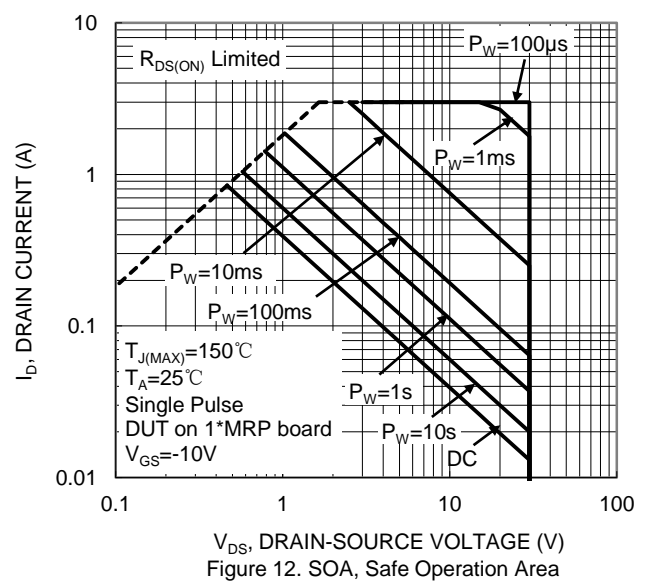
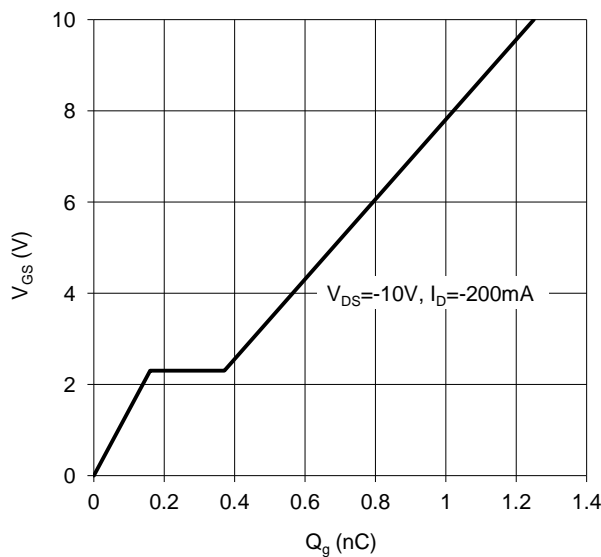
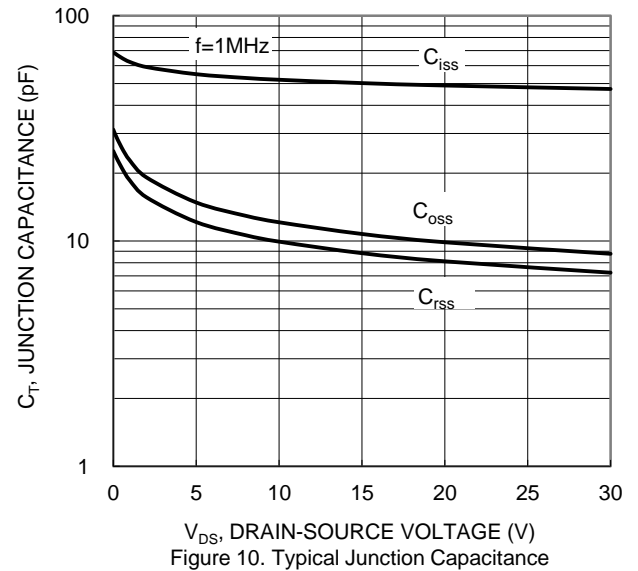
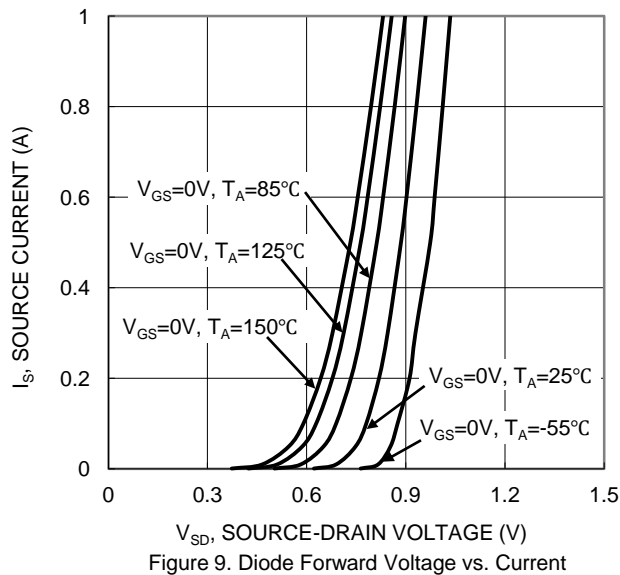
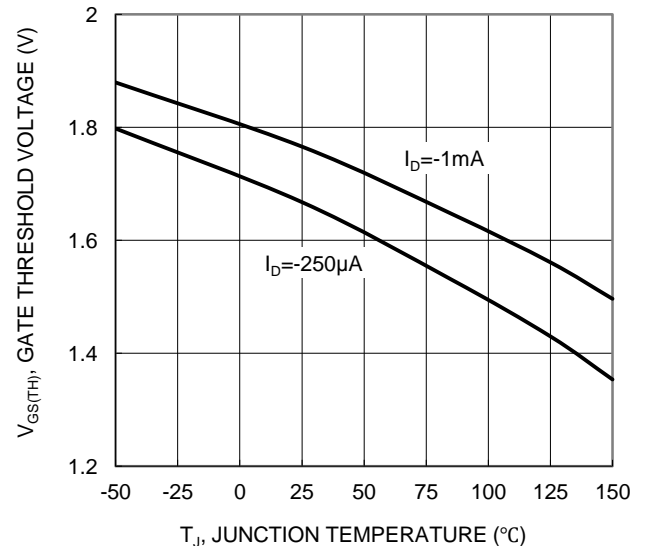
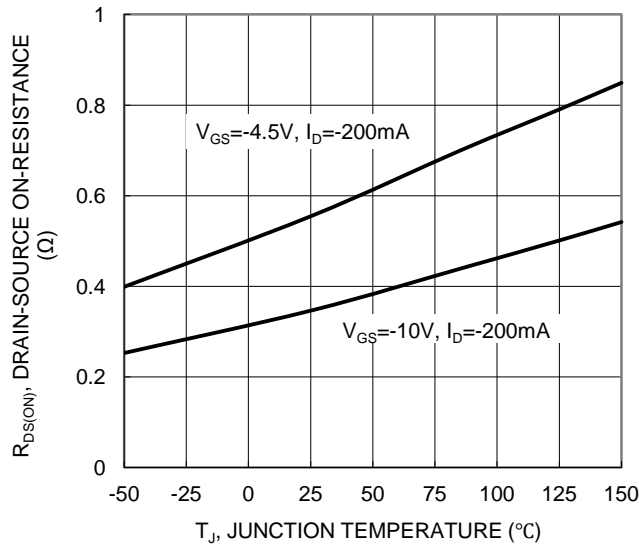
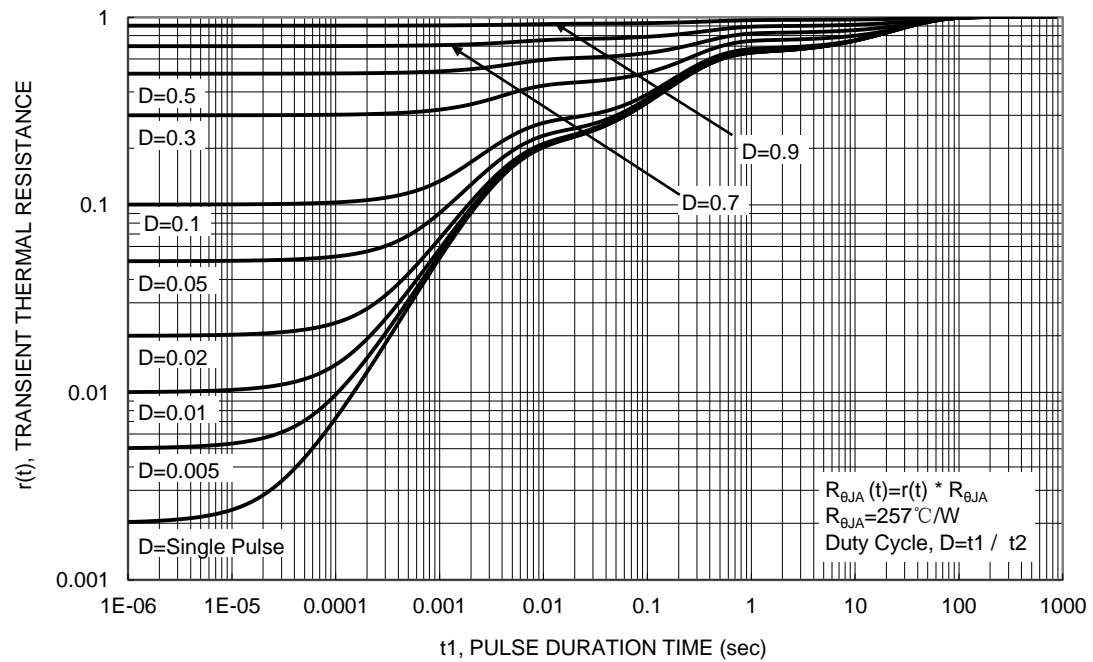


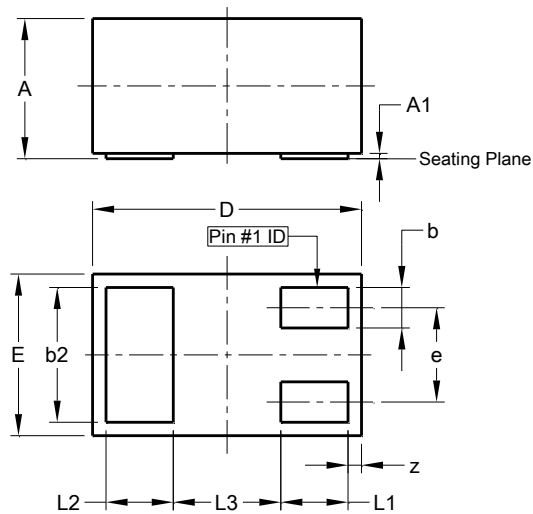
Figure 6. On-Resistance Variation with Temperature





## Package Outline Dimensions

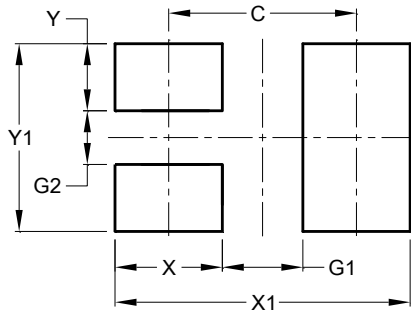
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
<b>C</b>	0.70
<b>G1</b>	0.30
<b>G2</b>	0.20
<b>X</b>	0.40
<b>X1</b>	1.10
<b>Y</b>	0.25
<b>Y1</b>	0.70

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